

CEZ6R86L-HF

N-Channel
RoHS Device
Halogen Free



BV _{DSS}	60V
I _D @V _{GS} =10V, T _C =25°C	56A
I _D @V _{GS} =10V, T _A =25°C	13.8A
R _{DS(ON)} @ V _{GS} =10V, I _D =25A	5.1mΩ(typ)
R _{DS(ON)} @ V _{GS} =4.5V, I _D =25A	7.4mΩ(typ)

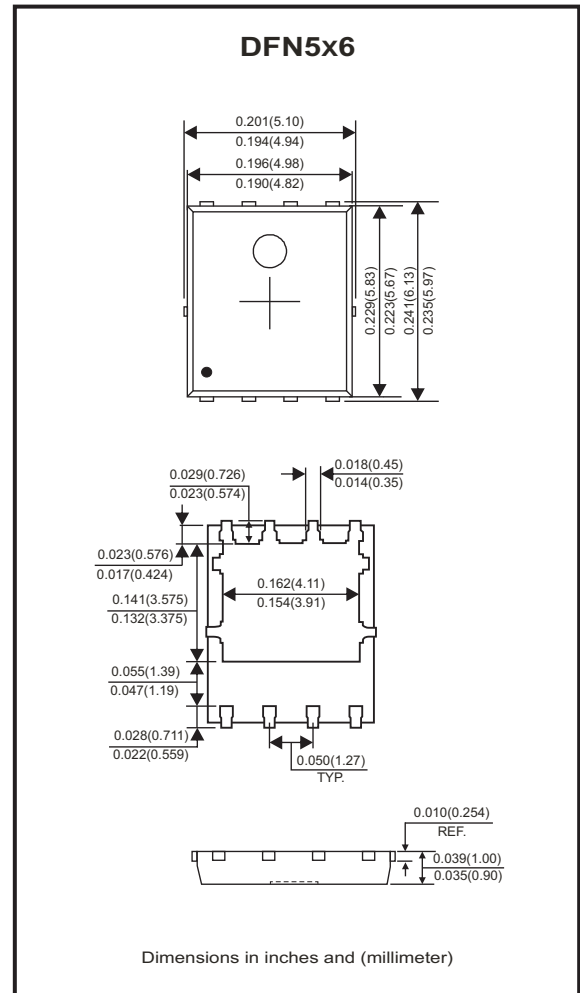
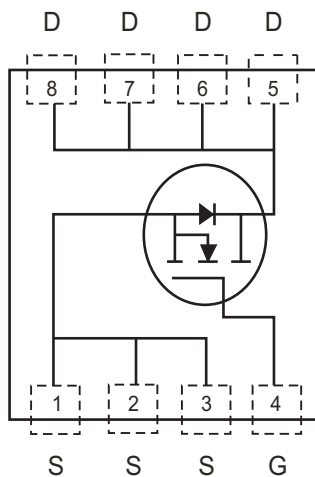
Features

- Single drive requirement.
- Low On-resistance
- Fast switching characteristic.
- Repetitive avalanche rated

Mechanical data

- Epoxy : UL 94V-0 rated flame retardant.
- Case : DFN5X6, molded plastic.
- Lead : Pure tin plated.

Circuit Diagram



Absolute Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	10s	Steady State	Unit	
Drain-source voltage	V _{DS}	60		V	
Gate-source voltage	V _{GS}	±20		V	
Drain current-continuous @ T _c =25°C, V _{GS} =10V (silicon limit) (Note 1)	I _D	80		A	
Continuous drain current @ T _c =25°C, V _{GS} =10V (package limit) (Note 1)		56		A	
Continuous drain current @ T _c =100°C, V _{GS} =10V (Note 1)		35		A	
Continuous drain current @ T _A =25°C, V _{GS} =10V (Note 2)	I _{DSM}	20.8	13.8	A	
Continuous drain current @ T _A =70°C, V _{GS} =10V (Note 2)		16.6	11.0	A	
Continuous drain current @ T _A =85°C, V _{GS} =10V (Note 2)		15.0	9.9	A	
Pulsed drain current (Note3)	I _{DM}	224 * 1		A	
Avalanche current (Note3)	I _{AS}	40		A	
Avalanche energy @ L=0.1mH, I _D =40A, V _{DD} =30V (Note 2,4)	E _{AS}	80		mJ	
Repetitive avalanche energy @ L=0.05mH (Note 3)	E _{AR}	10 * 2			
Total power dissipation	P _D	T _c =25°C (Note 1)	83		W
		T _c =100°C (Note 1)	33		
	P _D SM	T _A =25°C (Note 2)	5.7	2.5	
		T _A =70°C (Note 2)	4.0	1.8	
		T _A =85°C (Note 2)	3.6	1.6	
Operating temperature range	T _J	-55 to +150		°C	
Storage temperature range	T _{STG}	-55 to +150		°C	

Thermal Data

Parameter	Symbol	Typical	Maximum	Unit	
Thermal resistance, junction to ambient (Note 2)	R _{θJA}	t ≤ 10s	18	22	°C/W
		Steady state	42	50	°C/W
Thermal resistance junction to case	R _{θJC}	1.4	1.5	°C/W	

Notes: 1. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

- The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_DSM is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C
- 100% tested by conditions of L=0.1mH, I_{AS}=10A, V_{GS}=10V, V_{DD}=30V

Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	60			V
Gate-threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(th)}$	1.4		2.6	V
Forward transconductance (Note 1)	$V_{DS} = 10V, I_D = 30A$	G_{FS}		30		S
Gate-Source leakage current	$V_{GS} = \pm 20V$	I_{GSS}			± 100	nA
Zero gate voltage drain current	$V_{DS} = 48V, V_{GS} = 0V$	I_{DSS}			1	μA
	$V_{DS} = 48V, V_{GS} = 0V, T_J = 125^\circ C$	I_{DSS}			25	
Static drain-source on-resistance (Note 1)	$V_{GS} = 10V, I_D = 25A$	$R_{DS(on)}$		5.1	6.4	m Ω
	$V_{GS} = 4.5V, I_D = 25A$			7.4	9.6	
Dynamic						
Input capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	C_{iss}		1619		pF
Output capacitance		C_{oss}		275		
Reverse transfer capacitance		C_{rss}		143		
Total gate charge (Note 1,2)	$V_{DS} = 48V, V_{GS} = 10V, I_D = 25A$	Q_g		42.8		nC
Gate-source charge (Note 1,2)		Q_{gs}		5.8		
Gate-drain charge (Note 1,2)		Q_{gd}		15.6		
Turn-on delay time (Note 1,2)	$V_{DS} = 30V, I_D = 1A,$ $V_{GS} = 10V, R_{GS} = 6\Omega$	$t_{d(on)}$		15.2		ns
Turn-on rise time (Note 1,2)		t_r		22.4		
Turn-off delay time (Note 1,2)		$t_{d(off)}$		74		
Turn-off fall time (Note 1,2)		t_f		36		
Gate resistance	$f = 1MHz$	R_g		4		Ω
Source-Drain Diode						
Drain-source diode forward current (Note 1)		I_s			56	A
Pulse diode forward current (note3)		I_{SM}			224	
Drain-source diode forward voltage (Note 1)	$V_{GS} = 0V, I_s = 25A$	V_{SD}		0.82	1.2	V
Body Diode Reverse Recovery Time	$I_F = 25A, dI_F/dt = 100A/\mu s$	t_{rr}		18		nS
Body Diode Reverse Recovery Charge		Q_{rr}			12	

- Notes: 1. Pulse test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
 2. Independent of operating temperature
 3. Pulse width limited by maximum junction temperature.

RATING AND CHARACTERISTIC CURVES (CEZ6R86L-HF)

Fig.1 - Typical Output Characteristics

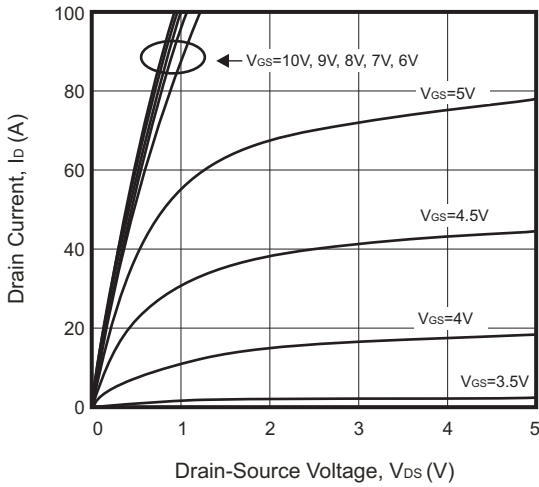


Fig.2 - Static Drain-Source On-State Resistance VS Drain Current

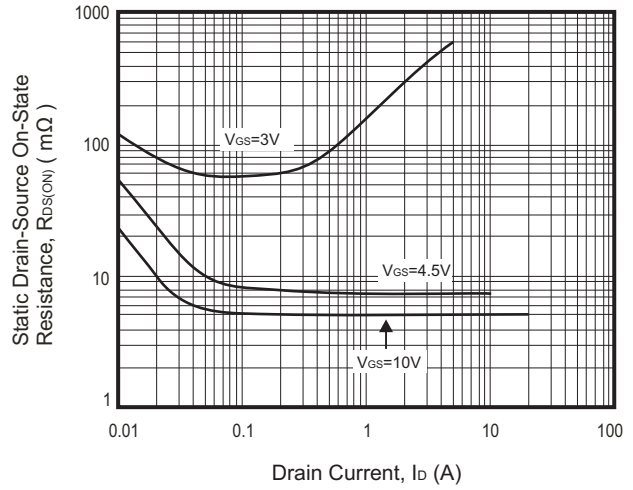


Fig.3 - Static Drain-Source On-State Resistance VS Gate-Source Voltage

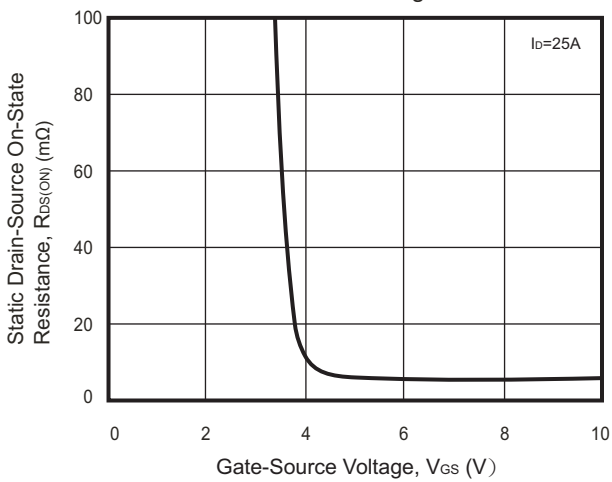


Fig.4 - Capacitance VS Drain-Source Voltage

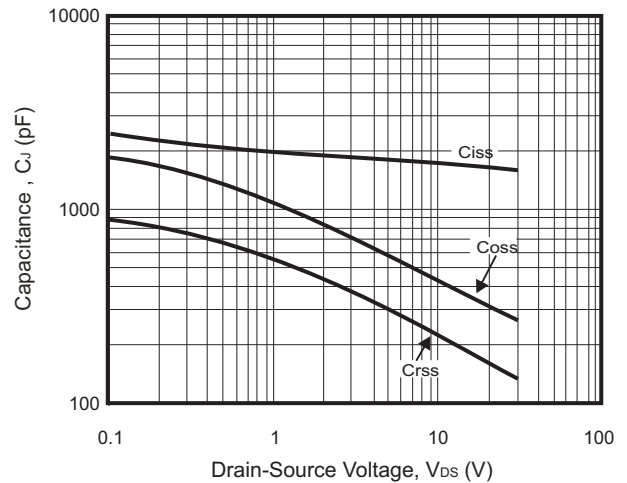


Fig.5 - Forward Transfer Admittance VS Drain Current

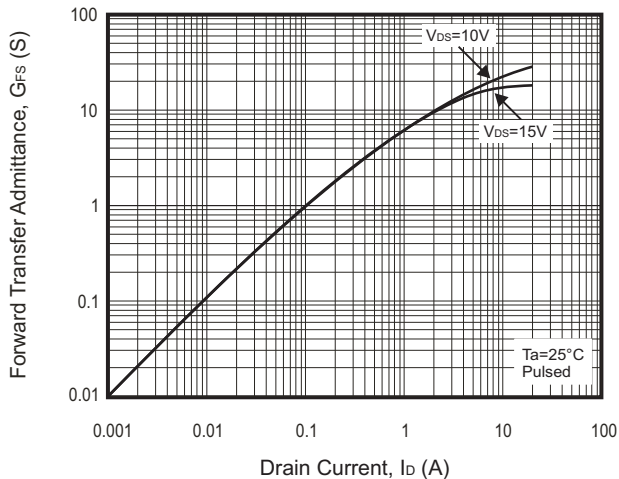
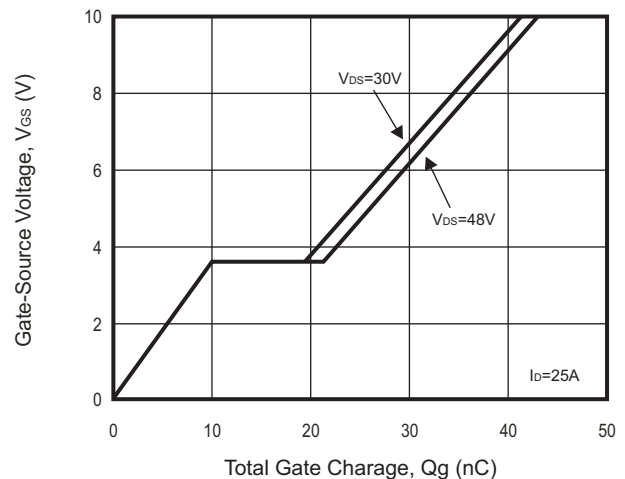
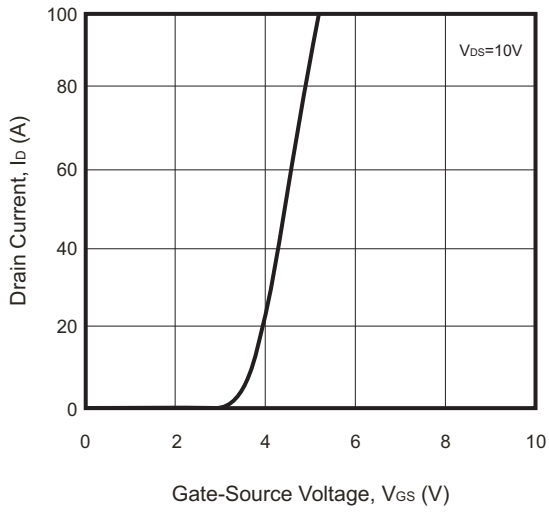


Fig.6 - Gate Charge Characteristics

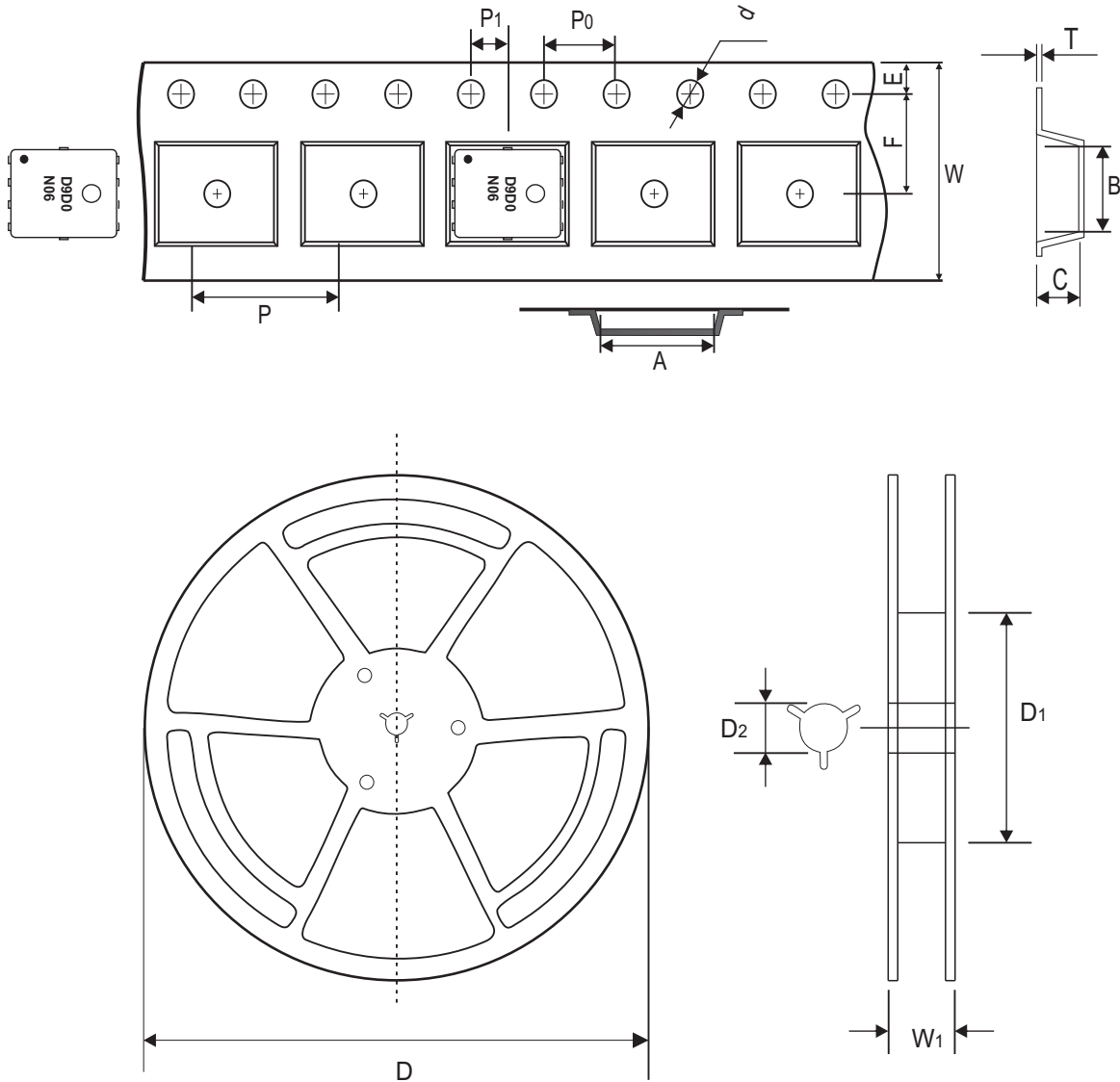


RATING AND CHARACTERISTIC CURVES (CEZ6R86L-HF)

Fig.7 - Typical Transfer Characteristics



Reel Taping Specification



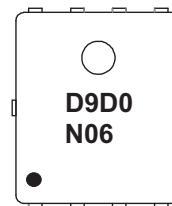
DFN5X6	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	6.30 ± 0.10	5.30 ± 0.10	1.10 ± 0.10	1.50 + 0.10 - 0.00	330.00 ± 1.00	100.00 ± 0.50	13.00 ± 0.20
	(inch)	0.248 ± 0.004	0.209 ± 0.004	0.043 ± 0.004	0.059 + 0.004 - 0.000	12.992 ± 0.039	3.937 ± 0.020	0.512 ± 0.008

DFN5X6	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	5.50 ± 0.05	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	0.25 ± 0.02	12.00 + 0.30 - 0.10	17.60 + 1.00 - 0.00
	(inch)	0.069 ± 0.004	0.217 ± 0.002	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.002	0.010 ± 0.001	0.472 + 0.012 - 0.004	0.693 + 0.039 - 0.000

Company reserves the right to improve product design , functions and reliability without notice.

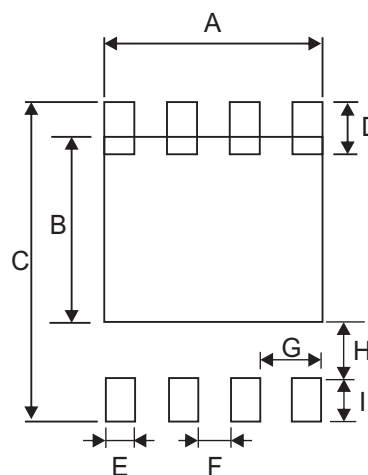
Marking Code

Part Number	Marking Code
CEZ6R86L-HF	D9D0N06



Suggested PAD Layout

SIZE	DFN5X6	
	(mm)	(inch)
A	4.42	0.174
B	3.81	0.150
C	6.61	0.260
D	1.02	0.040
E	0.61	0.024
F	0.66	0.026
G	1.27	0.050
H	1.23	0.048
I	0.86	0.034



Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
DFN5X6	3,000	13